

General Description

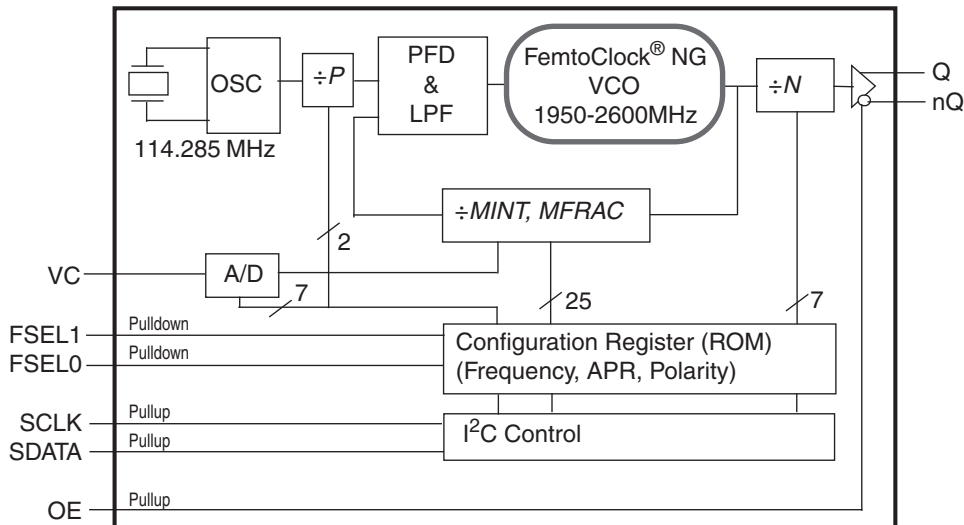
The IDT8N4QV01 is a Quad-Frequency Programmable VCXO with very flexible frequency and pull-range programming capabilities. The device uses IDT's fourth generation FemtoClock® NG technology for an optimum of high clock frequency and low phase noise performance. The device accepts 2.5V or 3.3V supply and is packaged in a small, lead-free (RoHS 6) 10-lead ceramic 5mm x 7mm x 1.55mm package.

Besides the 4 default power-up frequencies set by the FSEL0 and FSEL1 pins, the IDT8N4QV01 can be programmed via the I²C interface to any output clock frequency between 15.476MHz to 866.67MHz and from 975MHz to 1,300MHz to a very high degree of precision with a frequency step size of $435.9\text{Hz} \div N$ (N is the PLL output divider). Since the FSEL0 and FSEL1 pins are mapped to 4 independent PLL, P, M and N divider registers (P, MINT, MFRAC and N), reprogramming those registers to other frequencies under control of FSEL0 and FSEL1 is supported. The extended temperature range supports wireless infrastructure, tele-communication and networking end equipment requirements.

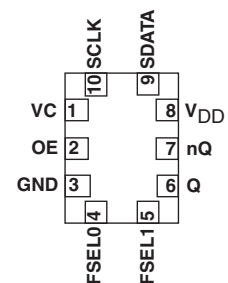
Features

- Fourth generation FemtoClock® NG technology
- Programmable clock output frequency from 15.476MHz to 866.67MHz and from 975MHz to 1,300MHz
- Four power-up default frequencies (see part number order codes), re-programmable by I²C
- I²C programming interface for the output clock frequency, APR and internal PLL control registers
- Frequency programming resolution is $435.9\text{Hz} \div N$
- Absolute pull-range (APR) programmable from $\pm 4.5\text{ppm}$ to $\pm 754.5\text{ppm}$
- One 2.5V or 3.3V LVDS differential clock output
- Two control inputs for the power-up default frequency
- LVCMOS/LVTTL compatible control inputs
- RMS phase jitter @ 156.25MHz (12kHz - 20MHz): 0.494ps (typical)
- RMS phase jitter @ 156.25MHz (1kHz - 40MHz): 0.594ps (typical)
- 2.5V or 3.3V supply voltage modes
- -40°C to 85°C ambient operating temperature
- Lead-free (RoHS 6) packaging

Block Diagram



Pin Assignment



IDT8N4QV01 REV G DATA SHEET
10-lead ceramic 5mm x 7mm x 1.55mm
package body
CD Package
Top View

Table 1. Pin Descriptions

| Number | Name | Type | | Description |
|--------|-----------------|--------|----------|--|
| 1 | VC | Input | | VCXO Control Voltage. The control voltage versus frequency characteristics are set by the ADC_GAIN[5:0] register bits. |
| 2 | OE | Input | Pullup | Output enable pin. See Table 3B for function. LVCMOS/LVTTL interface levels. |
| 3 | GND | Power | | Power supply ground. |
| 4, 5 | FSEL0, FSEL1 | Input | Pulldown | Default frequency select pins. See Table 3A for function and Table 8 for the default frequency order codes. LVCMOS/LVTTL interface levels. |
| 6, 7 | Q, nQ | Output | | Differential clock output. LVDS interface levels. |
| 8 | V _{DD} | Power | | Power supply pin. |
| 9 | SDATA | Input | Pullup | I ² C Data Input. LVCMOS/LVTTL interface levels. |
| 10 | SCLK | Input | Pullup | I ² C Clock Input. LVCMOS/LVTTL interface levels. |

NOTE: *Pullup* and *Pulldown* refer to internal input resistors. See Table 2, *Pin Characteristics*, for typical values.

Table 2. Pin Characteristics

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|-----------------------|-------------------------|------------------------|---------|---------|---------|-------|
| C _{IN} | Input Capacitance | FSEL[1:0], SDATA, SCLK | | 5.5 | | pF |
| | | VC | | 10 | | pF |
| R _{PULLUP} | Input Pullup Resistor | | | 50 | | kΩ |
| R _{PULLDOWN} | Input Pulldown Resistor | | | 50 | | kΩ |

Function Tables

Table 3A. Default Frequency Selection

| Input | | Operation |
|-------------|-------------|---------------------|
| FSEL1 | FSEL0 | |
| 0 (default) | 0 (default) | Default frequency 0 |
| 0 | 1 | Default frequency 1 |
| 1 | 0 | Default frequency 2 |
| 1 | 1 | Default frequency 3 |

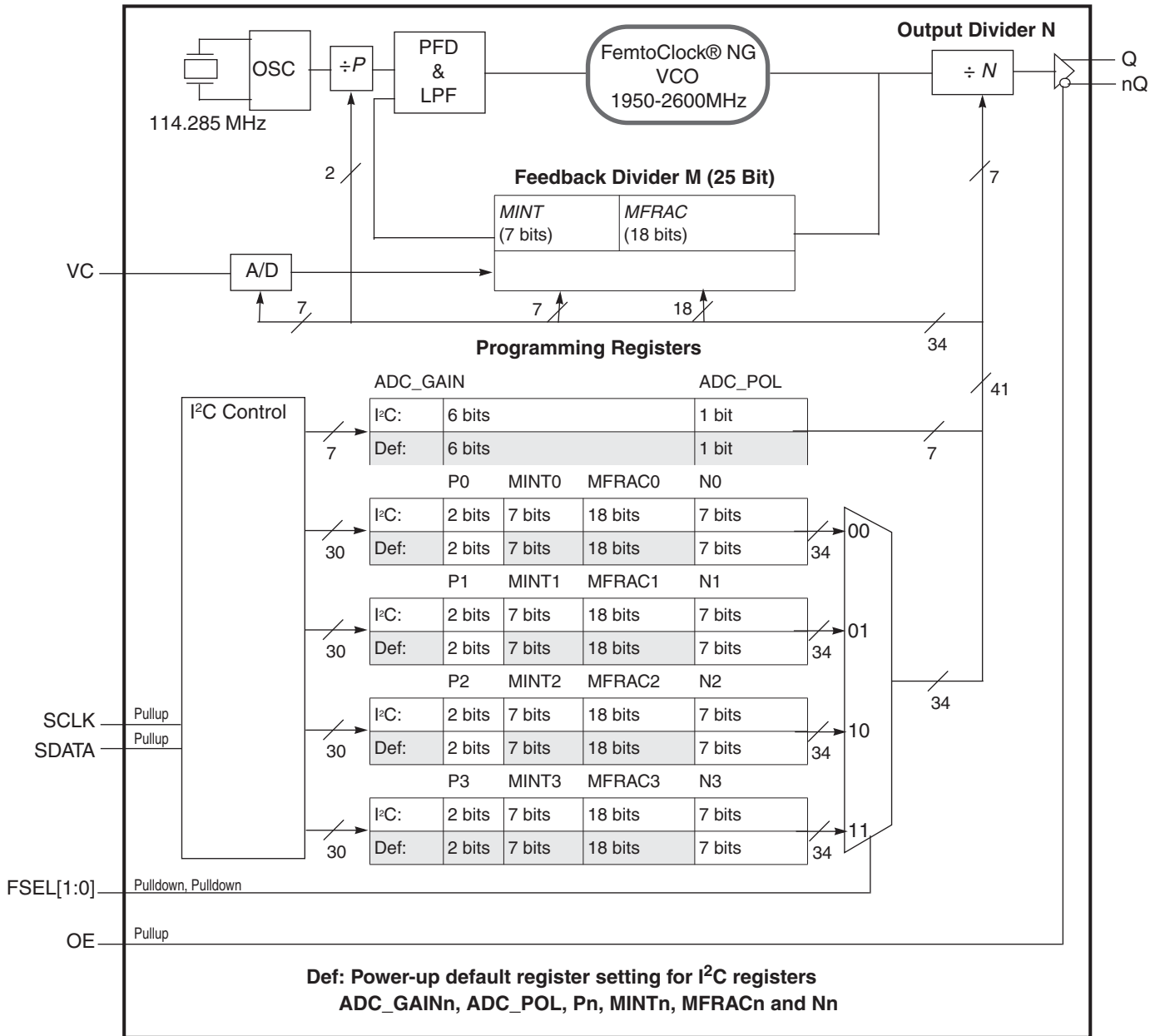
NOTE: The default frequency is the output frequency after power-up. One of four default frequencies is selected by FSEL[1:0]. See programming section for details.

Table 3B. OE Configuration

| Input | Output Enable |
|-------------|--|
| OE | |
| 0 | Outputs Q, nQ are in high-impedance state. |
| 1 (default) | Outputs are enabled. |

NOTE: OE is an asynchronous control.

Block Diagram with Programming Registers



Principles of Operation

The block diagram consists of the internal 3rd overtone crystal and oscillator which provide the reference clock f_{XTAL} of either 114.285MHz or 100MHz. The PLL includes the FemtoClock NG VCO along with the Pre-divider (P), the feedback divider (M) and the post divider (N). The P , M , and N dividers determine the output frequency based on the f_{XTAL} reference and must be configured correctly for proper operation. The feedback divider is fractional supporting a huge number of output frequencies. The configuration of the feedback divider to integer-only values results in an improved output phase noise characteristics at the expense of the range of output frequencies. In addition, internal registers are used to hold up to four different factory pre-set P , M , and N configuration settings. These default pre-sets are stored in the I²C registers at power-up. Each configuration is selected via the FSEL[1:0] pins and can be read back using the SCLK and SDATA pins.

The user may choose to operate the device at an output frequency different than that set by the factory. After power-up, the user may write new P , N and M settings into one or more of the four configuration registers and then use the FSEL[1:0] pins to select the newly programmed configuration. Note that the I²C registers are volatile and a power supply cycle will reload the pre-set factory default conditions.

If the user does choose to write a different P , M , and N configuration, it is recommended to write to a configuration which is not currently selected by FSEL[1:0] and then change to that configuration after the I²C transaction has completed. Changing the FSEL[1:0] controls results in an immediate change of the output frequency to the selected register values. The P , M , and N frequency configurations support an output frequency range 15.476MHz to 866.67MHz and 975MHz to 1,300MHz.

The devices use the fractional feedback divider with a delta-sigma modulator for noise shaping and robust frequency synthesis capability. The relatively high reference frequency minimizes phase noise generated by frequency multiplication and allows more efficient shaping of noise by the delta-sigma modulator.

The output frequency is determined by the 2-bit pre-divider (P), the feedback divider (M) and the 7-bit post divider (N). The feedback divider (M) consists of both a 7-bit integer portion ($MINT$) and an 18-bit fractional portion ($MFRAC$) and provides the means for high-resolution frequency generation. The output frequency f_{OUT} is calculated by:

$$f_{OUT} = f_{XTAL} \cdot \frac{1}{P \cdot N} \cdot \left[MINT + \frac{MFRAC + 0.5}{2^{18}} \right] \quad (1)$$

The four configuration registers for the P , M ($MINT$ & $MFRAC$) and N dividers which are named P_n , $MINT_n$, $MFRAC_n$ and N_n with $n = 0$ to 3. “ n ” denominates one of the four possible configurations.

As identified previously, the configurations of P , M ($MINT$ & $MFRAC$) and N divider settings are stored the I²C register, and the configuration loaded at power-up is determined by the FSEL[1:0] pins.

Table 4. Frequency Selection

| Input | | Selects | Register |
|----------|----------|-------------|-----------------------|
| FSEL1 | FSEL0 | | |
| 0 (def.) | 0 (def.) | Frequency 0 | P0, MINT0, MFRAC0, N0 |
| 0 | 1 | Frequency 1 | P1, MINT1, MFRAC1, N1 |
| 1 | 0 | Frequency 2 | P2, MINT2, MFRAC2, N2 |
| 1 | 1 | Frequency 3 | P3, MINT3, MFRAC3, N3 |

Frequency Configuration

An order code is assigned to each frequency configuration programmed by the factory (default frequencies). For more information on the available default frequencies and order codes, please see the Ordering Information Section in this document. For available order codes, see the *FemtoClock NG Ceramic-Package XO and VCXO Ordering Product Information* document.

For more information and guidelines on programming of the device for custom frequency configurations, the register description, the pull-range programming and the serial interface description, see the *FemtoClock NG Ceramic 5x7 Module Programming Guide*.

Absolute Maximum Ratings

NOTE: Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the *DC Characteristics* or *AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

| Item | Rating |
|--|--------------------------|
| Supply Voltage, V_{DD} | 3.63V |
| Inputs, V_I | -0.5V to $V_{DD} + 0.5V$ |
| Outputs, I_O (SDATA) Outputs, I_O (LVDS) Continuous Current Surge Current | 10mA 10mA 15mA |
| Package Thermal Impedance, θ_{JA} | 49.4°C/W (0 mps) |
| Storage Temperature, T_{STG} | -65°C to 150°C |

DC Electrical Characteristics

Table 5A. Power Supply DC Characteristics, $V_{DD} = 3.3V \pm 5\%$, $T_A = -40^\circ C$ to $85^\circ C$

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|----------|----------------------|-----------------|---------|---------|---------|-------|
| V_{DD} | Power Supply Voltage | | 3.135 | 3.3 | 3.465 | V |
| I_{DD} | Power Supply Current | | | | 160 | mA |

Table 5B. Power Supply DC Characteristics, $V_{DD} = 2.5V \pm 5\%$, $T_A = -40^\circ C$ to $85^\circ C$

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|----------|----------------------|-----------------|---------|---------|---------|-------|
| V_{DD} | Power Supply Voltage | | 2.375 | 2.5 | 2.625 | V |
| I_{DD} | Power Supply Current | | | | 155 | mA |

Table 5C. LVCMOS/LVTTL DC Characteristic, $V_{DD} = 3.3V \pm 5\%$ or $2.5V \pm 5\%$, $T_A = -40^\circ C$ to $85^\circ C$

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|----------|--------------------|-----------------|--|---------|----------------|---------|
| V_{IH} | Input High Voltage | SEL [1:0], OE | $V_{CC} = 3.3V + 5\%$ | 1.7 | $V_{CC} + 0.3$ | V |
| | | SEL [1:0], OE | $V_{CC} = 2.5V + 5\%$ | 1.7 | $V_{CC} + 0.3$ | V |
| V_{IL} | Input Low Voltage | SEL [1:0] | $V_{CC} = 3.3V + 5\%$ | -0.3 | 0.5 | V |
| | | OE | $V_{CC} = 3.3V + 5\%$ | -0.3 | 0.8 | V |
| | | SEL [1:0] | $V_{CC} = 2.5V + 5\%$ | -0.3 | 0.5 | V |
| | | OE | $V_{CC} = 2.5V + 5\%$ | -0.3 | 0.8 | V |
| I_{IH} | Input High Current | OE | | | 10 | μA |
| | | SDATA, SCLK | $V_{DD} = V_{IN} = 3.465V$ or $2.625V$ | | 5 | μA |
| | | FSEL0, FSEL1 | $V_{DD} = V_{IN} = 3.465V$ or $2.625V$ | | 150 | μA |
| I_{IL} | Input Low Current | OE | | -500 | | μA |
| | | SDATA, SCLK | $V_{DD} = 3.465V$ or $2.625V$, $V_{IN} = 0V$ | -150 | | μA |
| | | FSEL0, FSEL1 | $V_{DD} = 3.465V$ or $2.625V$, $V_{IN} = 0V$ | -5 | | μA |

Table 5D. LVDS DC Characteristics, $V_{DD} = 3.3V \pm 5\%$ or $2.5V \pm 5\%$, $T_A = -40^\circ C$ to $85^\circ C$

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|-----------------|-----------------------------|-----------------|---------|---------|---------|-------|
| V_{OD} | Differential Output Voltage | | 247 | 350 | 454 | mV |
| ΔV_{OD} | V_{OD} Magnitude Change | | | | 50 | mV |
| V_{OS} | Offset Voltage | | 1.0 | 1.20 | 1.375 | V |
| ΔV_{OS} | V_{OS} Magnitude Change | | | | 50 | mV |

AC Electrical Characteristics

Table 6A. VCXO Control Voltage Input (V_C) Characteristics, $V_{DD} = 3.3V \pm 5\%$ or $2.5V \pm 5\%$, $T_A = -40^\circ C$ to $85^\circ C$

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units | |
|---------------|--|------------------------|---------|--|--|------------|-------|
| K_V | Oscillator Gain, NOTE 1, 2, 3 $V_{DD} = 3.3V$ | ADC_GAIN[5:0] = 000001 | | 7.57 | | ppm/V | |
| | | ADC_GAIN[5:0] = 000010 | | 15.15 | | ppm/V | |
| | | ADC_GAIN[5:0] = XXXXXX | | $2 \cdot 12.5 \div V_{DD}$ ADC_GAIN | | ppm/V | |
| | | ADC_GAIN[5:0] = 111110 | | 469.69 | | ppm/V | |
| | | ADC_GAIN[5:0] = 111111 | | 477.27 | | ppm/V | |
| | Oscillator Gain, NOTE 1, 2, 3 $V_{DD} = 2.5V$ | ADC_GAIN[5:0] = 000001 | | | 10 | | ppm/V |
| | | ADC_GAIN[5:0] = 000010 | | | 20 | | ppm/V |
| | | ADC_GAIN[5:0] = XXXXXX | | | $2 \cdot 12.5 \div V_{DD}$ ADC_GAIN | | ppm/V |
| | | ADC_GAIN[5:0] = 111110 | | | 620 | | ppm/V |
| | | ADC_GAIN[5:0] = 111111 | | | 630 | | ppm/V |
| L_{VC} | Control Voltage Linearity | BSL Variation; NOTE 4 | -5 | ± 1 | +5 | % | |
| | | Incremental; NOTE 5 | -10 | ± 5 | +10 | % | |
| BW | Modulation Bandwidth | | | 100 | | kHz | |
| Z_{VC} | VC Input Impedance | | | 500 | | k Ω | |
| $V_{C_{NOM}}$ | Nominal Control Voltage | | | $V_{DD} \div 2$ | | V | |
| V_C | Control Voltage Tuning Range; NOTE 4 | | 0 | | V_{DD} | V | |

NOTE: Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lfm. The device will meet specifications after thermal equilibrium has been reached under these conditions.

NOTE 1: $V_C = 0V$ to V_{DD} .

NOTE 2: Nominal oscillator gain: Pull range divided by the control voltage tuning range of 3.3V.

E.g. for ADC_GAIN[6:0] = 00.0001 the pull range is $\pm 12.5\text{ppm}$, resulting in an oscillator gain of $2 * 12.5\text{ppm} \div 3.3V = 7.57\text{ppm/V}$.

NOTE 3: For best phase noise performance, use the lowest K_V that meets the requirements of the application.

NOTE 4: BSL = Best Straight Line Fit: Variation of the output frequency vs. control voltage V_C , in percent. V_C ranges from 10% to 90% V_{DD} .

NOTE 5: Incremental slope is defined as the linearity in percent of the raw data (not relative to BSL) from 10% to 90% V_{DD} .

Table 6B. AC Characteristics, $V_{DD} = 3.3V \pm 5\%$ or $2.5V \pm 5\%$, $T_A = -40^\circ C$ to $85^\circ C$

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|----------------------|--|---|---------|---------|-----------|---------|
| f_{OUT} | Output Frequency Q, nQ | Output Divider, $N = 3$ to 126 | 15.476 | | 866.67 | MHz |
| | | Output Divider, $N = 2$ | 975 | | 1,300 | MHz |
| f_{VCO} | VCO Frequency | | 1980 | | 2600 | MHz |
| f_I | Initial Accuracy | Measured at $25^\circ C$ | | | ± 10 | ppm |
| f_S | Temperature Stability | Option code = A or B | | | ± 100 | ppm |
| | | Option code = E or F | | | ± 50 | ppm |
| | | Option code = K or L | | | ± 20 | ppm |
| f_A | Aging | Frequency drift over 10 year life | | | ± 3 | ppm |
| | | Frequency drift over 15 year life | | | ± 5 | ppm |
| f_T | Total Stability | Option code A or B (10 year life) | | | ± 113 | ppm |
| | | Option code E or F (10 year life) | | | ± 63 | ppm |
| | | Option code K or L (10 year life) | | | ± 33 | ppm |
| $f_{jit(cc)}$ | Cycle-to-Cycle Jitter; NOTE 1 | | | | 20 | ps |
| $f_{jit(per)}$ | Period Jitter; NOTE 1 | | | 2.85 | 4 | ps |
| $f_{jit(\emptyset)}$ | RMS Phase Jitter (Random) Fractional PLL feedback and $f_{XTAL} = 114.285MHz$ (0xxx order codes) | $17MHz \leq f_{OUT} \leq 1300MHz$, NOTE 2,3,4 | | 0.475 | 0.990 | ps |
| | | $f_{OUT} = 156.25MHz$, NOTE 2, 3, 4 | | 0.494 | 0.757 | ps |
| | | $f_{OUT} = 156.25MHz$, NOTE 2, 3, 5 | | 0.594 | | ps |
| $\Phi_N(100)$ | Single-side band phase noise, 100 Hz from Carrier | 156.25MHz | | -73.8 | | dBc/Hz |
| $\Phi_N(1k)$ | Single-side band phase noise, 1kHz from Carrier | 156.25MHz | | -99.8 | | dBc/Hz |
| $\Phi_N(10k)$ | Single-side band phase noise, 10kHz from Carrier | 156.25MHz | | -126.1 | | dBc/Hz |
| $\Phi_N(100k)$ | Single-side band phase noise, 100kHz from Carrier | 156.25MHz | | -129.3 | | dBc/Hz |
| $\Phi_N(1M)$ | Single-side band phase noise, 1MHz from Carrier | 156.25MHz | | -140.3 | | dBc/Hz |
| $\Phi_N(10M)$ | Single-side band phase noise, 10MHz from Carrier | 156.25MHz | | -144.3 | | dBc/Hz |
| PSNR | Power Supply Noise Rejection | 50mV Sinusoidal Noise 1kHz - 50MHz | | -54 | | db |
| t_R / t_F | Output Rise/Fall Time | 20% to 80% | 100 | | 425 | ps |
| odc | Output Duty Cycle | | 45 | | 55 | % |
| t_{OSC} | Oscillator Start-Up Time | | | | 20 | ms |
| t_{SET} | Output Frequency Settling Time after FSEL0 and FSEL1 Values are Changed | | | 470 | | μs |

NOTE: Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lfm. The device will meet specifications after thermal equilibrium has been reached under these conditions. All AC parameters are characterized with P=1 and pull range ± 250 ppm.

NOTE: XTAL parameters (initial accuracy, temperature stability, aging and total stability) are guaranteed by manufacturing.

NOTE 1: This parameter is defined in accordance with JEDEC standard 65.

NOTE 2: Please refer to the phase noise plots.

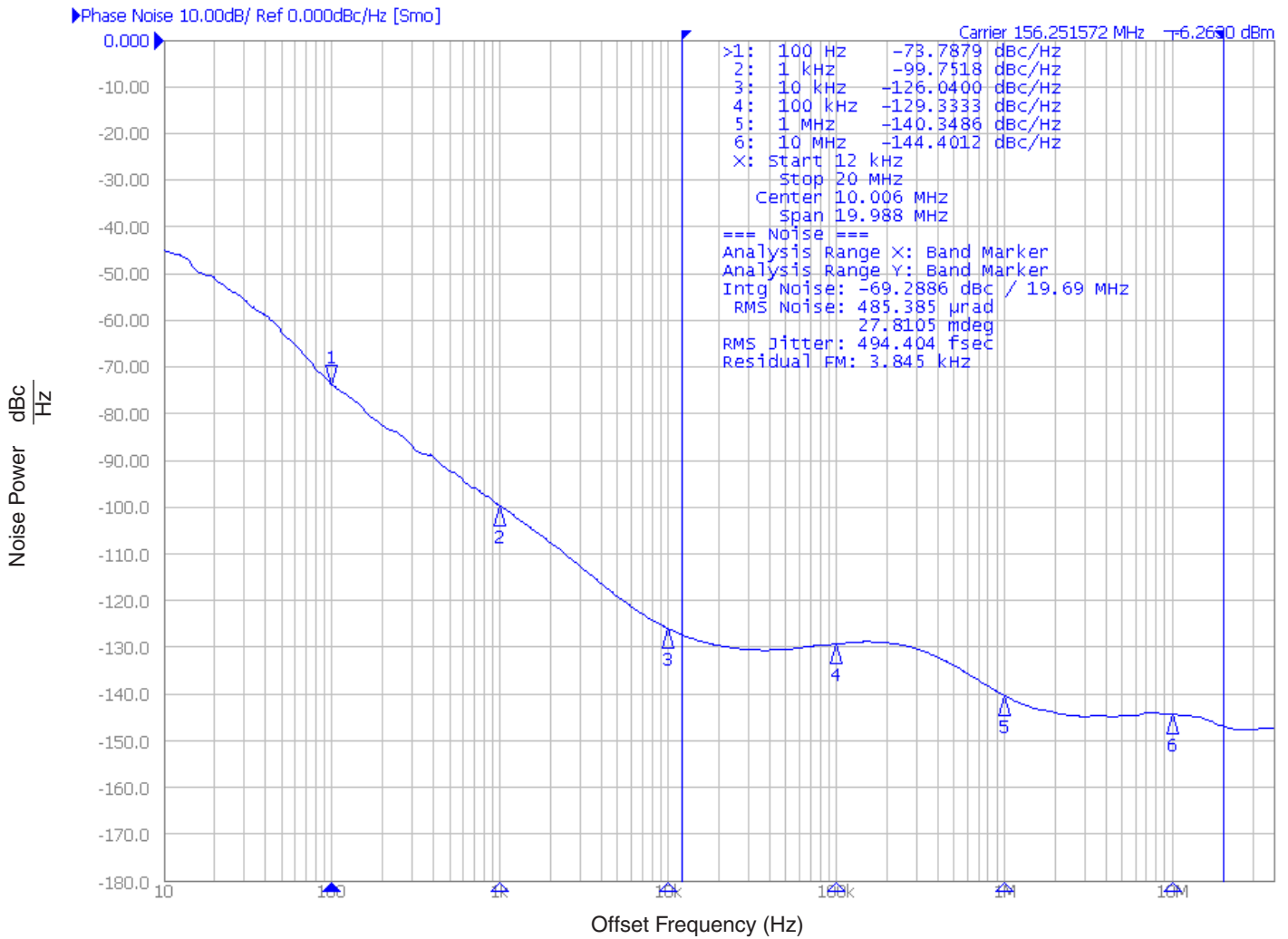
NOTES continued on next page.

NOTE 3: Please see the FemtoClock NG Ceramic 5x7 Modules Programming guide for more information on finding the optimum configuration for phase noise.

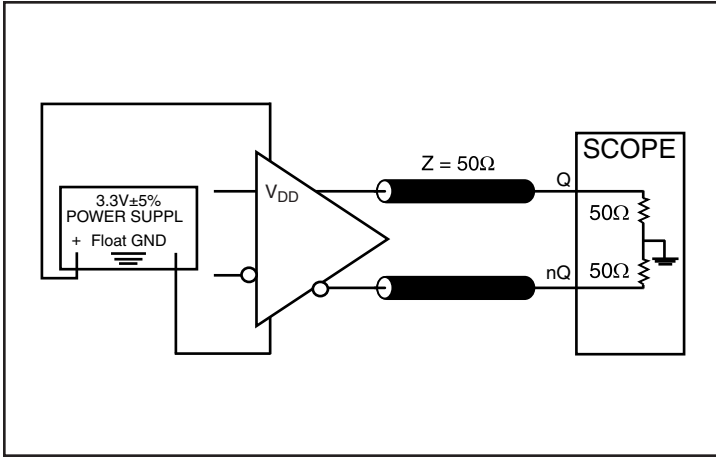
NOTE 4: Integration range: 12kHz-20MHz.

NOTE 5: Integration range: 1kHz-40MHz.

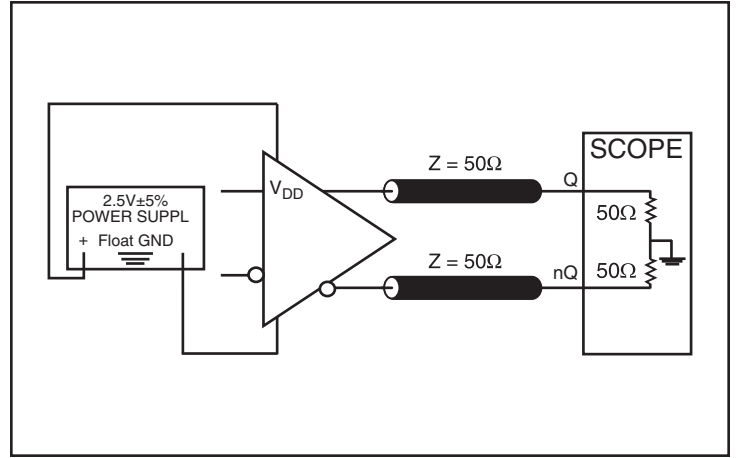
Typical Phase Noise at 156.25MHz (12kHz - 20MHz)



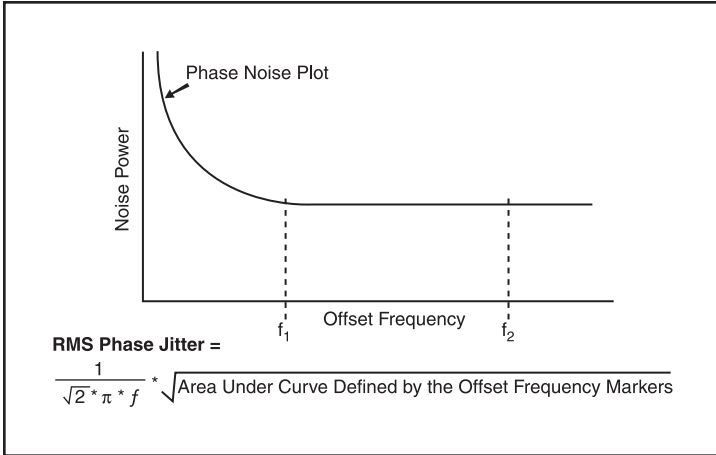
Parameter Measurement Information



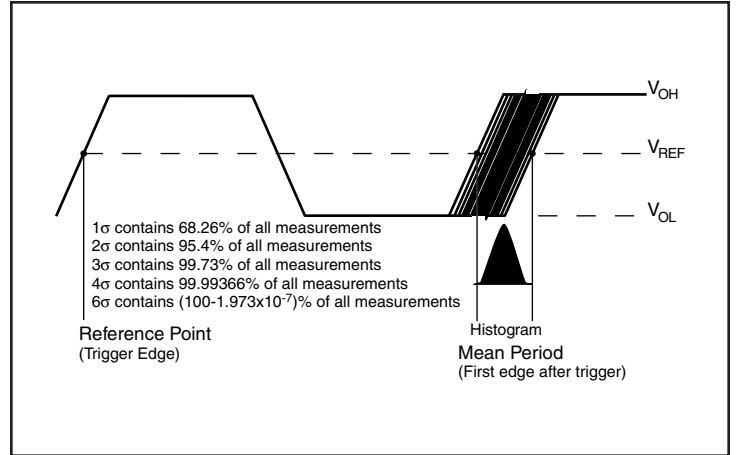
3.3V LVDS Output Load AC Test Circuit



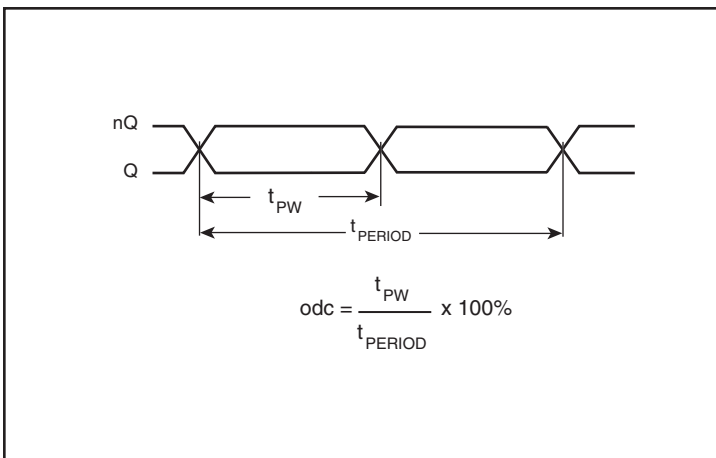
2.5V LVDS Output Load AC Test Circuit



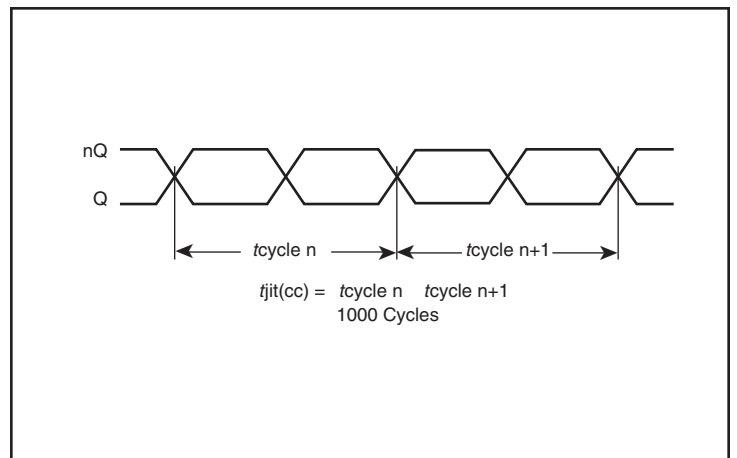
RMS Phase Jitter



Period Jitter

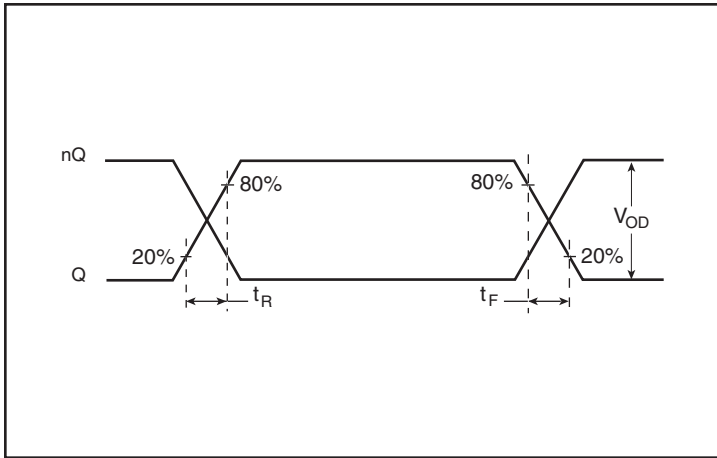


Output Duty Cycle/Pulse Width/Period

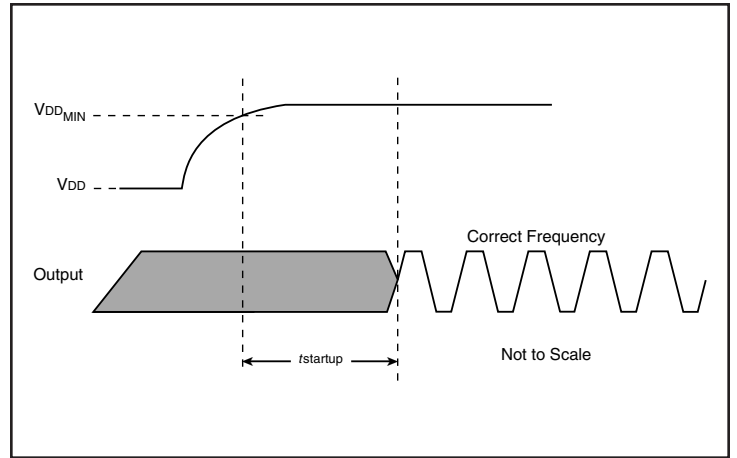


Cycle-to-Cycle Jitter

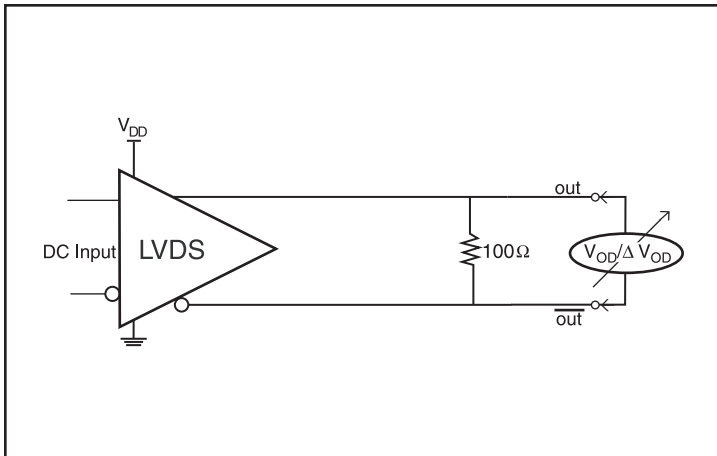
Parameter Measurement Information (continued)



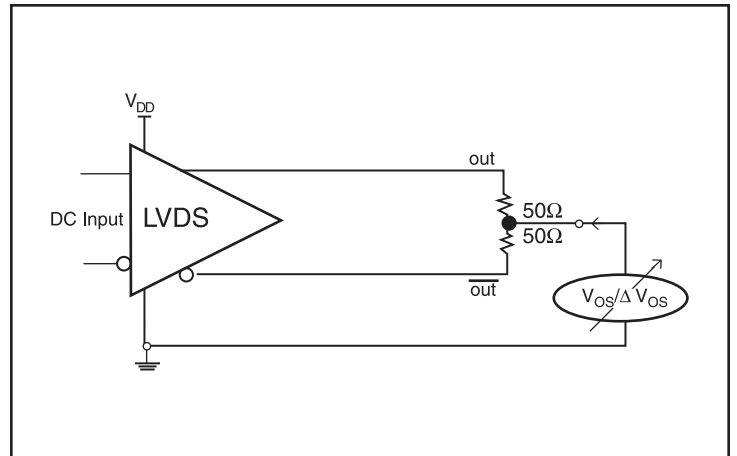
Output Rise/Fall Time



Start-Up



Differential Output Voltage Setup



Offset Voltage Setup

Applications Information

Recommendations for Unused Input Pins

Inputs:

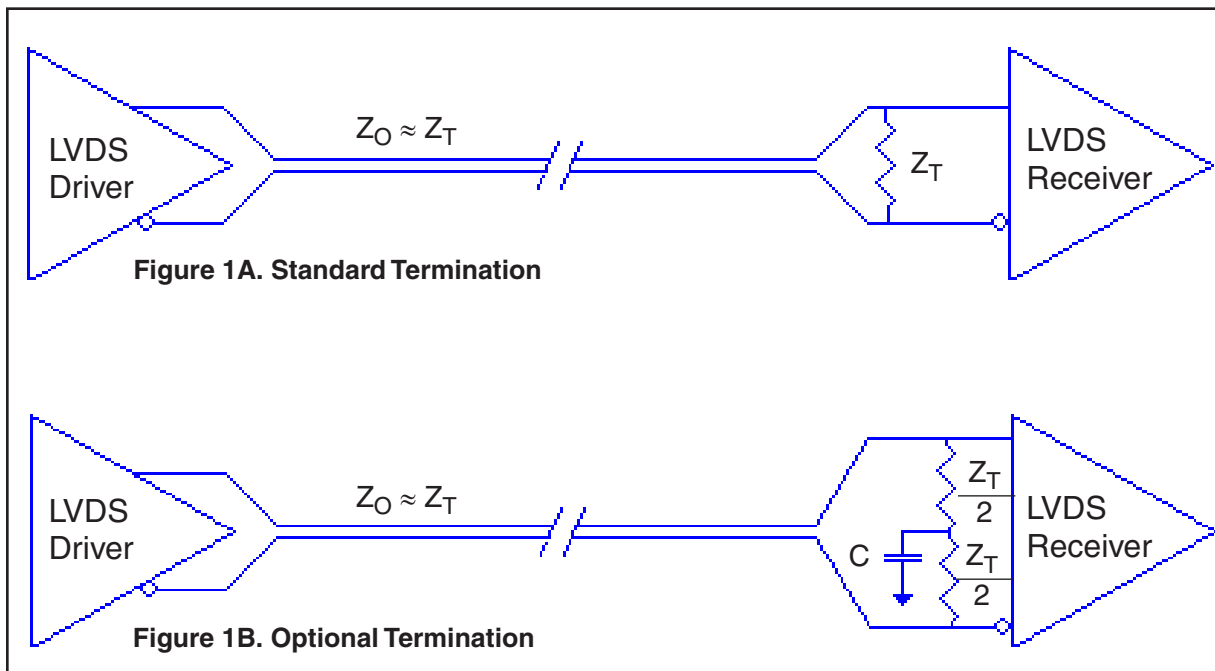
LVCMOS Select Pins

All control pins have internal pulldowns; additional resistance is not required but can be added for additional protection. A 1kΩ resistor can be used.

LVDS Driver Termination

For a general LVDS interface, the recommended value for the termination impedance (Z_T) is between 90Ω and 132Ω. The actual value should be selected to match the differential impedance (Z_0) of your transmission line. A typical point-to-point LVDS design uses a 100Ω parallel resistor at the receiver and a 100Ω differential transmission-line environment. In order to avoid any transmission-line reflection issues, the components should be surface mounted and must be placed as close to the receiver as possible. IDT offers a full line of LVDS compliant devices with two types of output structures: current source and voltage source. The

standard termination schematic as shown in *Figure 1A* can be used with either type of output structure. *Figure 1B*, which can also be used with both output types, is an optional termination with center tap capacitance to help filter common mode noise. The capacitor value should be approximately 50pF. If using a non-standard termination, it is recommended to contact IDT and confirm if the output structure is current source or voltage source type. In addition, since these outputs are LVDS compatible, the input receiver's amplitude and common-mode input range should be verified for compatibility with the output.



LVDS Termination

Power Considerations

This section provides information on power dissipation and junction temperature for the IDT8N4QV01. Equations and example calculations are also provided.

1. Power Dissipation.

The total power dissipation for the IDT8N4QV01 is the sum of the core power plus the power dissipated in the load(s). The following is the power dissipation for $V_{DD} = 3.3V + 5\% = 3.465V$, which gives worst case results.

- Power (core)_{MAX} = $V_{DD_MAX} * I_{DD_MAX} = 3.465V * 160mA = 554.4mW$

2. Junction Temperature.

Junction temperature, T_j , is the temperature at the junction of the bond wire and bond pad directly affects the reliability of the device. The maximum recommended junction temperature is 125°C. Limiting the internal transistor junction temperature, T_j , to 125°C ensures that the bond wire and bond pad temperature remains below 125°C.

The equation for T_j is as follows: $T_j = \theta_{JA} * Pd_total + T_A$

T_j = Junction Temperature

θ_{JA} = Junction-to-Ambient Thermal Resistance

Pd_total = Total Device Power Dissipation (example calculation is in section 1 above)

T_A = Ambient Temperature

In order to calculate junction temperature, the appropriate junction-to-ambient thermal resistance θ_{JA} must be used. Assuming no air flow and a multi-layer board, the appropriate value is 49.4°C/W per Table 7 below.

Therefore, T_j for an ambient temperature of 85°C with all outputs switching is:

$$85^\circ\text{C} + 0.554\text{W} * 49.4^\circ\text{C/W} = 112.4^\circ\text{C}. \text{ This is below the limit of } 125^\circ\text{C}.$$

This calculation is only an example. T_j will obviously vary depending on the number of loaded outputs, supply voltage, air flow and the type of board (multi-layer).

Table 7. Thermal Resistance θ_{JA} for 10 Lead Ceramic 5mm x 7mm Package, Forced Convection

| θ_{JA} by Velocity | | | |
|---|----------|----------|--------|
| Meters per Second | 0 | 1 | 2.5 |
| Multi-Layer PCB, JEDEC Standard Test Boards | 49.4°C/W | 44.2°C/W | 41°C/W |

Reliability Information

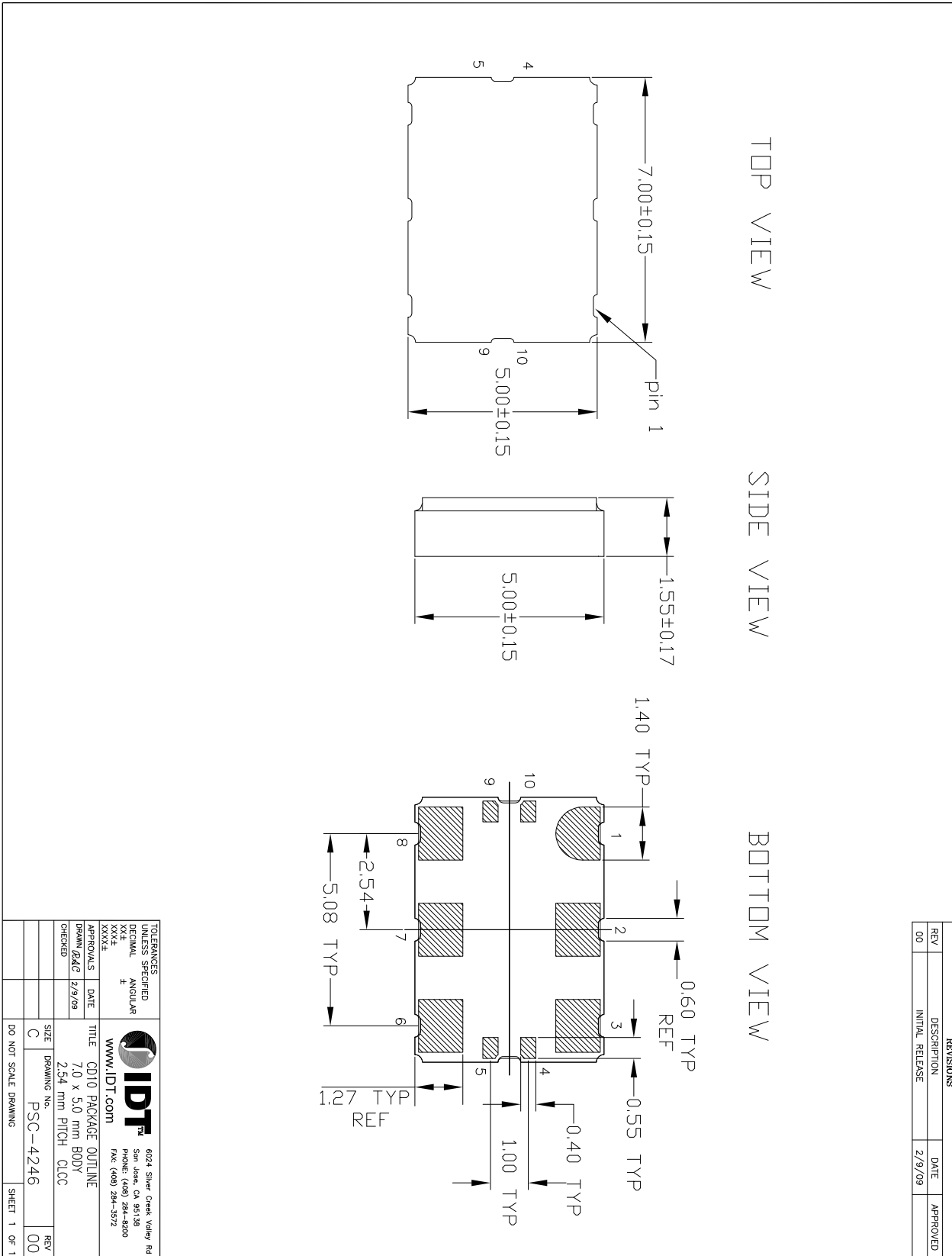
Table 8. θ_{JA} vs. Air Flow Table for a 10-lead Ceramic 5mm x 7mm Package

| θ_{JA} vs. Air Flow | | | |
|---|----------|----------|--------|
| Meters per Second | 0 | 1 | 2.5 |
| Multi-Layer PCB, JEDEC Standard Test Boards | 49.4°C/W | 44.2°C/W | 41°C/W |

Transistor Count

The transistor count for IDT8N4QV01 is: 47,372

Package Outline and Package Dimensions



| REVISIONS | | | |
|-----------|-----------------|--------|----------|
| REV | DESCRIPTION | DATE | APPROVED |
| 00 | INITIAL RELEASE | 2/9/09 | |

| | | | |
|-----------------------------|---------|---|---|
| TOLERANCES UNLESS SPECIFIED | | | 6024 Silver Creek Valley Rd San Jose, CA 95138 PHONE: (408) 284-8200 FAX: (408) 284-3572 |
| DECIMAL | ANGULAR | | |
| XXXX | E | WWW.IDT.COM | |
| DATE | TITLE | CD10 PACKAGE OUTLINE 7.0 x 5.0 mm BODY 2.54 mm PITCH CLCC | |
| 2/9/09 | DRW:GAC | SIZE | REV |
| CHECKED | | C | 00 |
| | | DRAWING No. | PSC-4246 |

DO NOT SCALE DRAWING

SHEET 1 OF 1

Ordering Information for FemtoClock NG Ceramic-Package XO and VCXO Products

The programmable VCXO and XO devices support a variety of device options such as the output type, number of default frequencies, internal crystal frequency, power supply voltage, ambient temperature range and the frequency accuracy. The device options, default frequencies and default VCXO pull range must be specified at the time of order and are programmed by IDT before the shipment. The table below specifies the available order codes, including the device options and default frequency configurations. Example part number: the order code 8N3QV01FG-0001CDI specifies a programmable, quad default-frequency VCXO with a voltage supply of 2.5V, a LVPECL output, a ± 50 ppm crystal frequency accuracy,

contains a 114.285MHz internal crystal as frequency source, industrial temperature range, a lead-free (6/6 RoHS) 10-lead ceramic 5mm x 7mm x 1.55mm package and is factory-programmed to the default frequencies of 100, 122.88, 125 and 156.25MHz and to the VCXO pull range of min. ± 100 ppm.

Other default frequencies and order codes are available from IDT on request. For more information on available default frequencies, see the *FemtoClock NG Ceramic-Package XO and VCXO Ordering Product Information* document.

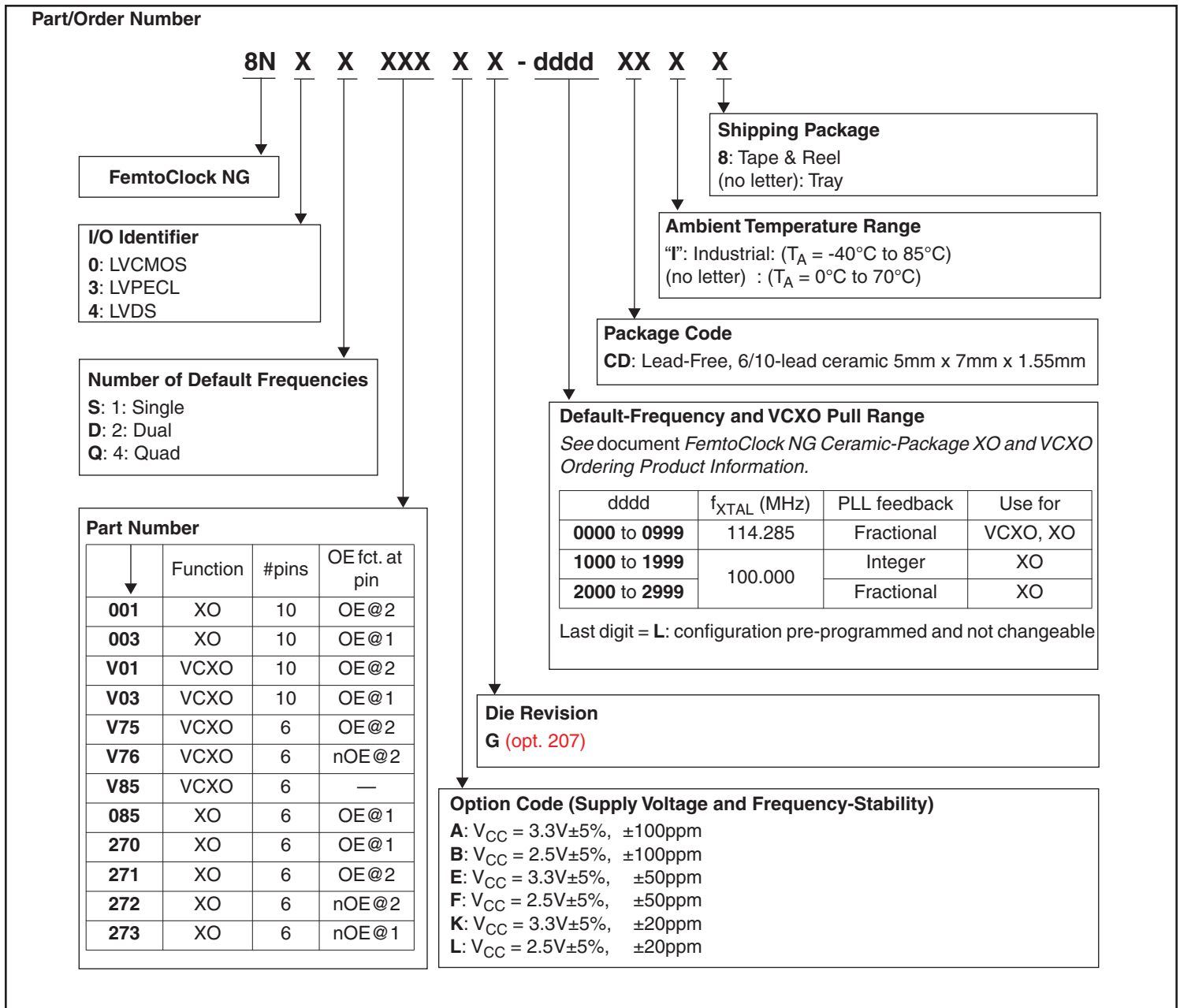


Table 9. Device Marking

| Marking | Industrial Temperature Range (T _A = -40°C to 85°C) | Commercial Temperature Range (T _A = 0°C to 70°C) |
|--|---|---|
| | | IDT8N4 x V01 y G- dddd CDI |
| x = Number of Default Frequencies, y = Option Code, dddd =Default-Frequency and VCXO Pull Range | | |

Revision History Sheet

| Rev | Table | Page | Description of Change | Date |
|-----|-----------|--------|--|---------|
| A | T9 | 18 | Table 9 Device Marking, corrected marking. | 3/6/12 |
| A | T1 T6A | 2 8 | Deleted "(see table 3C)" from the first table row, description column. NOTE 2; Deleted "from table 3C". | 3/13/14 |

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(Rev.4.0-1 November 2017)

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